



UM61512A Series

64K X 8 BIT HIGH SPEED CMOS SRAM

Features

- Single +5V power supply
- Access times: 15/20/25ns (max.)
- Current: Operating: 160mA (max.)
Standby: 10mA (max.)
- Full static operation, no clock or refreshing required
- All inputs and outputs are directly TTL compatible
- Common I/O using three-state output
- Output enable and two chip enable inputs for easy application
- Data retention voltage: 3V (min.)
- Available in 32-pin SKINNY DIP, TSOP, SOP, SOJ and both 300/400 mil packages

General Description

The UM61512A is a low operating current 524,288-bit static random access memory organized as 65,536 words by 8 bits and operates on a single 5V power supply. It is built using UMC's high performance CMOS process.

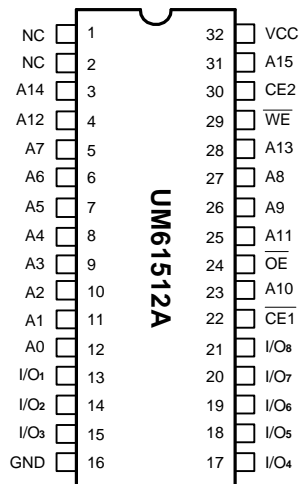
Inputs and three-state outputs are TTL compatible and allow for direct interfacing with common system bus structures.

Two chip enable inputs are provided for POWER-DOWN and device enable and an output enable input is included for easy interfacing.

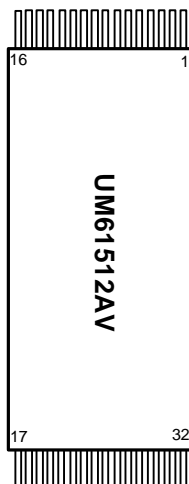
Data retention is guaranteed at a power supply voltage as low as 3V.

Pin Configurations

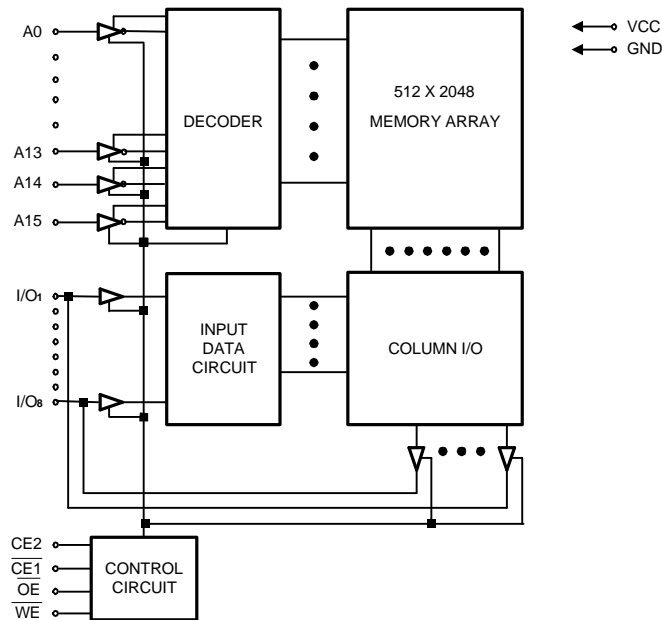
■ SKINNY/SOJ/SOP



■ TSOP (forward type)



Pin No.	Pin Name	Pin No.	Pin Name
1	A11	17	A3
2	A9	18	A2
3	A8	19	A1
4	A13	20	A0
5	WE	21	I/O ₁
6	CE2	22	I/O ₂
7	A15	23	I/O ₃
8	VCC	24	GND
9	NC	25	I/O ₄
10	NC	26	I/O ₅
11	A14	27	I/O ₆
12	A12	28	I/O ₇
13	A7	29	I/O ₈
14	A6	30	CE1
15	A5	31	A10
16	A4	32	OE

Block Diagram

Pin Descriptions SKINNY/SOJ/SOP

Pin No.	Symbol	Description
1, 2	NC	No Connection
3 - 12, 23, 25 - 28, 31	A0 - A15	Address Inputs
13 - 15, 17 - 21	I/O ₁ - I/O ₈	Data Input/Outputs
16	GND	Ground
22	$\overline{CE1}$	Chip Enable
24	\overline{OE}	Output Enable
29	\overline{WE}	Write Enable
30	CE2	Chip Enable
32	VCC	Power Supply

Pin Description TSOP

Pin No.	Symbol	Description
1 - 4, 7, 11 - 20, 31	A0 - A15	Address Inputs
5	\overline{WE}	Write Enable
6	CE2	Chip Enable
8	VCC	Power Supply
9, 10	NC	No Connection
21 - 23, 25 - 29	I/O ₁ - I/O ₈	Data Input/Outputs
24	GND	Ground
30	$\overline{CE1}$	Chip Enable
32	\overline{OE}	Output Enable

Recommended DC Operating Conditions ($T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$)

Symbol	Parameter	Min.	Typ.	Max.	Unit
VCC	Supply Voltage	4.75	5.0	5.25	V
GND	Ground	0	0	0	V
V _{IH}	Input High Voltage	2.2	3.5	VCC + 0.3	V
V _{IL}	Input Low Voltage	-0.3	0	+0.8	V
C _L	Output Load	-	-	30	pF
TTL	Output Load	-	-	1	-

Absolute Maximum Ratings*

VCC to GND -0.5V to +7.0V
 IN, IN/OUT Volt to GND -0.5V to VCC +0.5V
 Operating Temperature, Topr 0°C to $+70^\circ\text{C}$
 Storage Temperature, Tstg -55°C to $+125^\circ\text{C}$
 Temperature Under Bias, Tbias -10°C to $+85^\circ\text{C}$
 Power Dissipation, Pt 1.0W
 Soldering Temp. & Time 260°C , 10 sec

***Comments**

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to this device. These are stress ratings only. Functional operation of this device at these or any other conditions above those indicated in the operational sections of this specification is not implied or intended. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

DC Electrical Characteristics ($T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$, VCC = $5\text{V} \pm 5\%$, GND = 0V)

Symbol	Parameter	UM61512A-15/20/25		Unit	Conditions
		Min.	Max.		
I _{LI}	Input Leakage Current	-	2	μA	V _{IN} = GND to VCC
I _{LO}	Output Leakage Current	-	2	μA	$\overline{\text{CE1}} = V_{IH}$ or $\overline{\text{CE2}} = V_{IL}$ or $\overline{\text{OE}} = V_{IH}$ or $\overline{\text{WE}} = V_{IL}$ V _{IO} = GND to VCC
I _{CC1} (1)	Dynamic Operating Current	-	160	mA	$\overline{\text{CE1}} = V_{IL}$, $\overline{\text{CE2}} = V_{IH}$ I _{IO} = 0 mA
I _{SB}	Standby Power Supply Current	-	30	mA	$\overline{\text{CE1}} = V_{IH}$ or $\overline{\text{CE2}} = V_{IL}$
I _{SB1}		-	20	mA	$\overline{\text{CE1}} \geq V_{CC} - 0.2\text{V}$, $\overline{\text{CE2}} \geq V_{CC} - 0.2\text{V}$, V _{IN} $\leq 0.2\text{V}$ or V _{IN} $\geq V_{CC} - 0.2\text{V}$
I _{SB2}		-	20	mA	$\overline{\text{CE1}} \leq 0.2\text{V}$, $\overline{\text{CE2}} \leq 0.2\text{V}$ V _{IN} $\leq 0.2\text{V}$ or V _{IN} $\geq V_{CC} - 0.2\text{V}$
V _{OL}	Output Low Voltage	-	0.4	V	I _{OL} = 8 mA
V _{OH}	Output High Voltage	2.4	-	V	I _{OH} = -4 mA

Note: 1. I_{CC1} is dependent on output loading, cycle rates, and Read/Write patterns.

Truth Table

Mode	$\overline{CE1}$	CE2	\overline{OE}	\overline{WE}	I/O Operation	Supply Current
Standby	H	X	X	X	High Z	I_{SB}, I_{SB1}
	X	L	X	X	High Z	I_{SB}, I_{SB2}
Output Disable	L	H	H	H	High Z	I_{CC1}
Read	L	H	L	H	DOUT	I_{CC1}
Write	L	H	X	L	DIN	I_{CC1}

Note: X = H or L

Capacitance ($T_A = 25^\circ\text{C}$, $f = 1.0\text{ MHz}$)

Symbol	Parameter	Min.	Max.	Unit	Conditions
C_{IN}^*	Input Capacitance		8	pF	$V_{IN} = 0V$
C_{IO}^*	Input/Output Capacitance		10	pF	$V_{IO} = 0V$

* These parameters are sampled and not 100% tested.

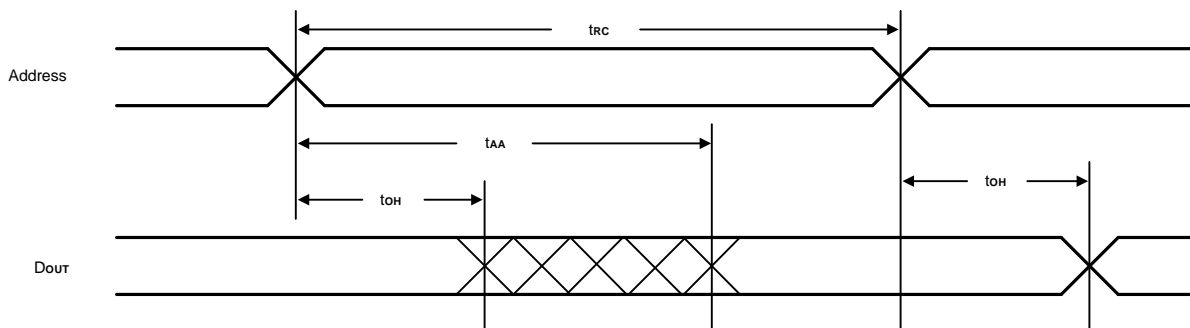
AC Characteristics ($T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$, $V_{CC} = 5V \pm 10\%$)

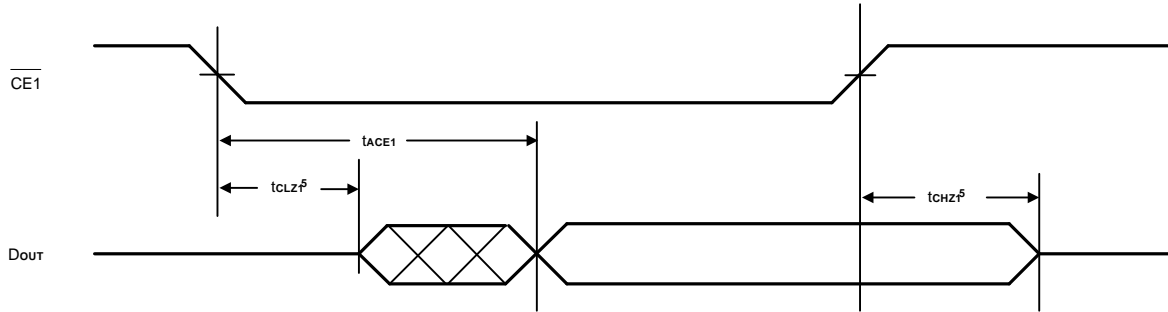
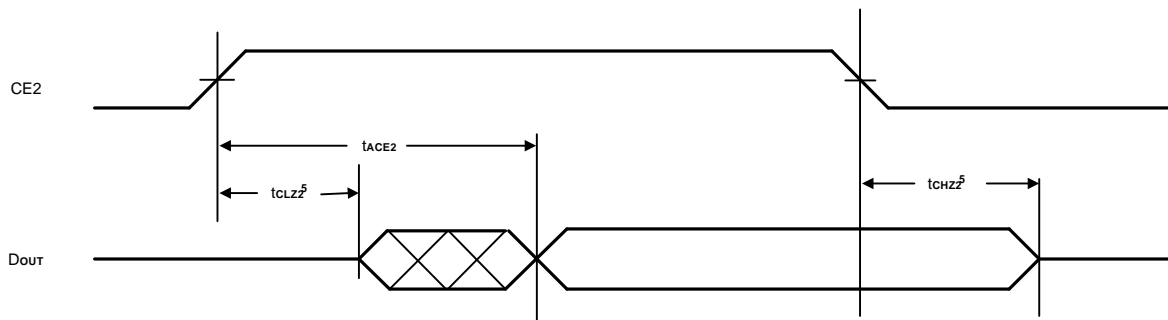
Symbol	Parameter	UM61512A-15		UM61512A-20		UM61512A-25		Unit	
		Min.	Max.	Min.	Max.	Min.	Max.		
Read Cycle									
t_{RC}	Read Cycle Time	15	-	20	-	25	-	ns	
t_{AA}	Address Access Time	-	15	-	20	-	25	ns	
t_{ACE1}	Chip Enable Access Time	$\overline{CE1}$	-	15	-	20	-	25	ns
t_{ACE2}		CE2	-	15	-	20	-	25	ns
t_{OE}	Output Enable to Output Valid	-	7	-	9	-	12	ns	
t_{CLZ1}	Chip Enable to Output in Low Z	$\overline{CE1}$	5	-	5	-	5	-	ns
t_{CLZ2}		CE2	5	-	5	*	5	-	ns
t_{OLZ}	Output Enable to Output in Low Z	2	-	2	-	2	-	ns	
t_{CHZ1}	Chip Disable to Output in High Z	$\overline{CE1}$	-	10	-	10	-	15	ns
t_{CHZ2}		CE2	-	10	-	10	-	15	ns
t_{OHZ}	Output Disable to Output in High Z	2	9	2	9	2	10	ns	
t_{OH}	Output Hold from Address Change	3	-	5	-	5	-	ns	

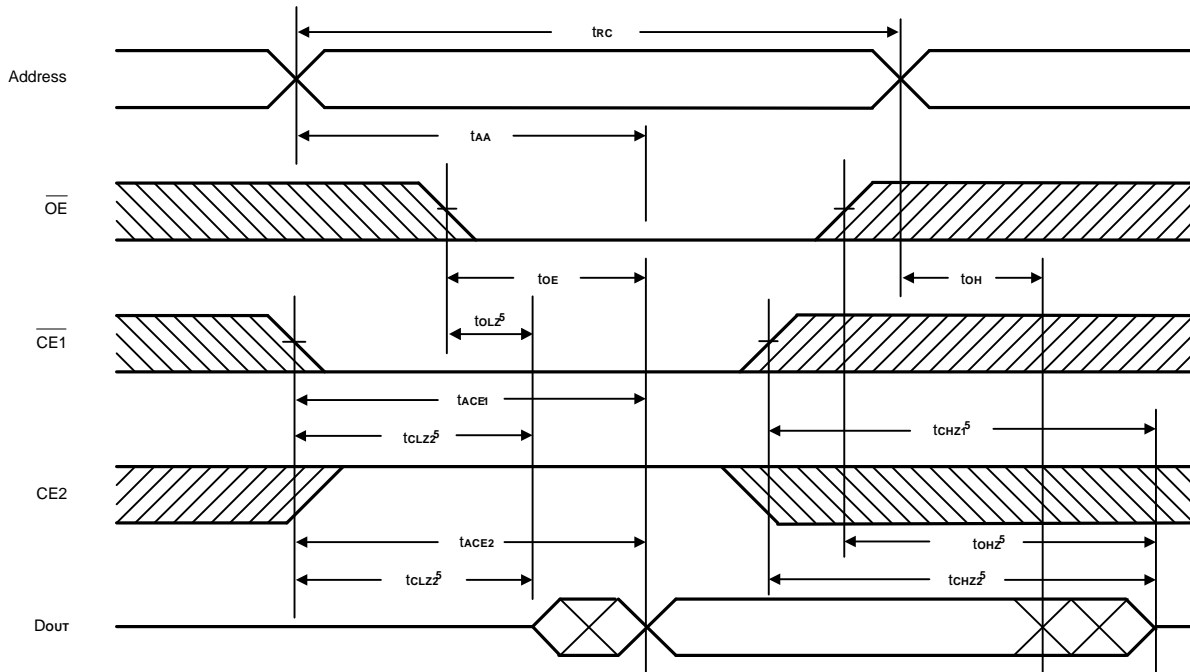
AC Characteristics (continued)

Symbol	Parameter	UM61512A-15		UM61512A-20		UM61512A-25		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
Write Cycle								
t _{wc}	Write Cycle Time	15	20	20	25	25	-	ns
t _{cw}	Chip Enable to End of Write	12	15	15	20	20	-	ns
t _{as}	Address Setup Time of Write	0	0	0	0	0	-	ns
t _{aw}	Address Valid to End of Write	12	15	15	20	20	-	ns
t _{wp}	Write Pulse Width	9	-	11	-	-	-	ns
t _{wr}	Write Recovery Time	0	-	0	-	-	-	ns
t _{whz}	Write to Output in High Z	0	8	0	13	13	13	ns
t _{dW}	Data to Write Time Overlap	7	-	7	-	-	-	ns
t _{dH}	Data Hold from Write Time	0	-	0	-	-	-	ns
t _{ow}	Output Active from End of Write	5	-	5	-	-	-	ns

Notes: t_{chz1}, t_{chz2}, t_{ohz} and t_{whz} are defined as the time at which the outputs achieve the open circuit condition and are not referred to output voltage levels.

Timing Waveforms
Read Cycle ^(1,2,4)


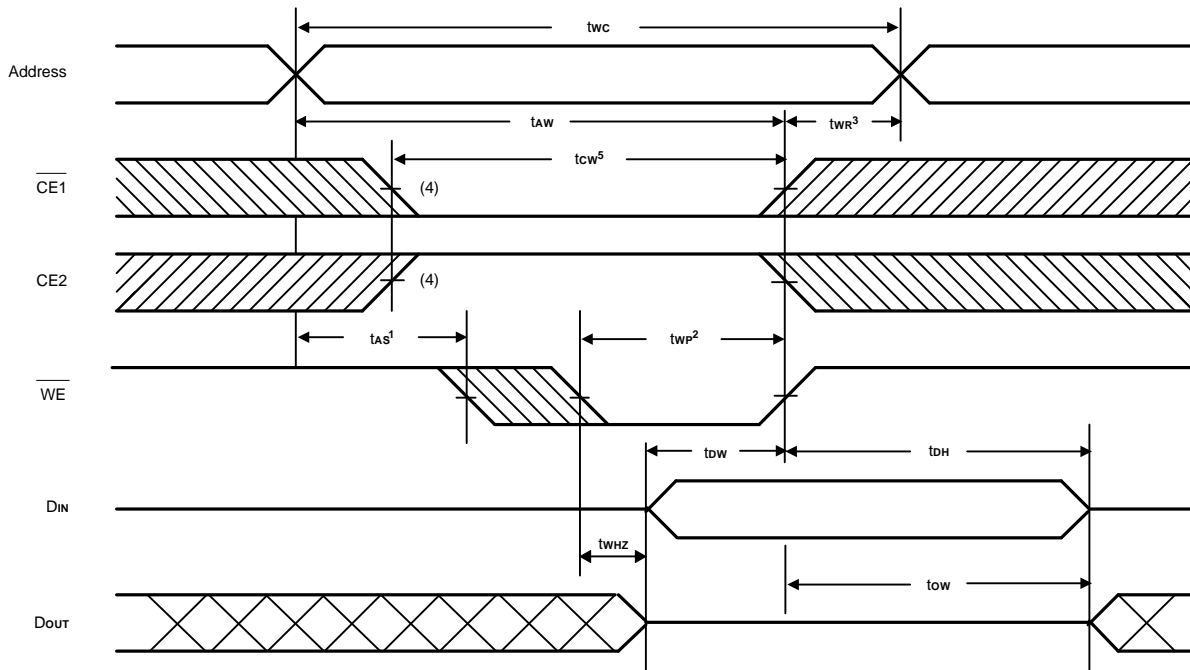
Timing Waveforms (continued)
Read Cycle 2^(1,3,4,6)

Read Cycle 3^(1,4,7,8)


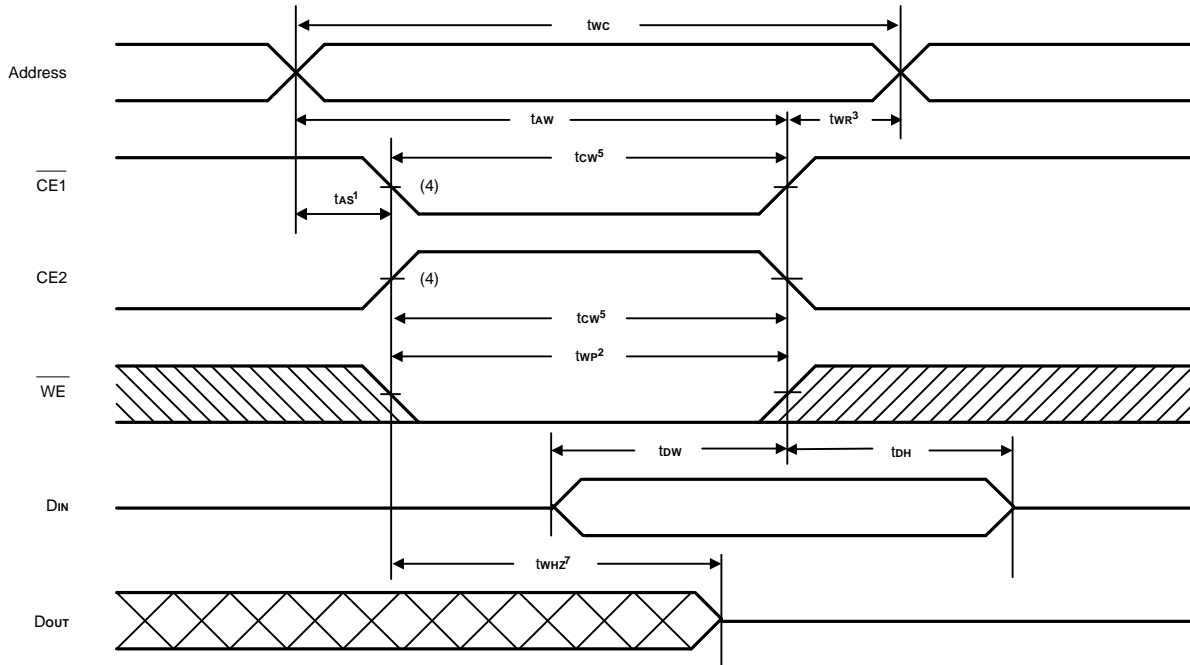
Timing Waveforms (continued)
Read Cycle 4⁽¹⁾


- Notes:
1. \overline{WE} is high for Read Cycle.
 2. Device is continuously enabled $\overline{CE1} = V_{IL}$ and $CE2 = V_{IH}$.
 3. Address valid prior to or coincident with $\overline{CE1}$ transition low.
 4. $\overline{OE} = V_{IL}$.
 5. Transition is measured $\pm 500\text{mV}$ from steady state. This parameter is sampled and not 100% tested.
 6. $CE2$ is high.
 7. $\overline{CE1}$ is low.
 8. Address valid prior to or coincident with $CE2$ transition high.

Timing Waveforms (continued)

Write Cycle 1⁽⁶⁾
(Write Enable Controlled)

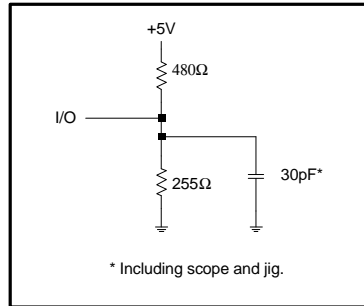
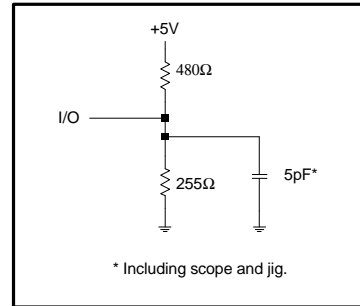


Timing Waveforms (continued)
**Write Cycle 2
(Chip Enable Controlled)**


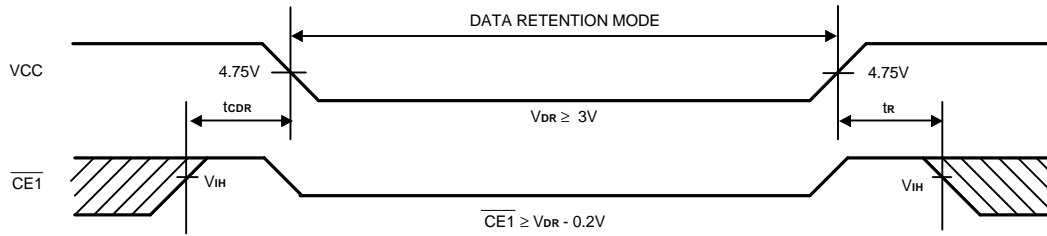
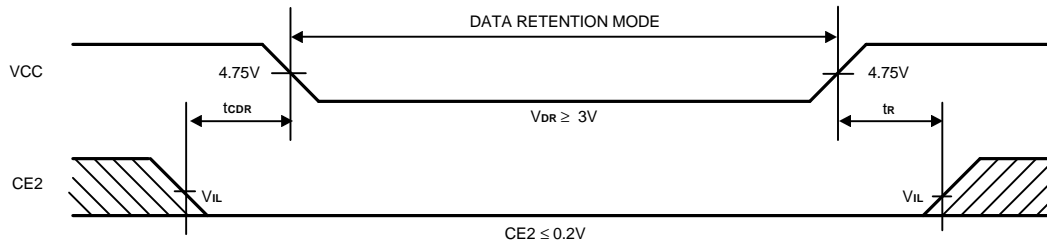
- Notes:
1. t_{AS} is measured from the address valid to the beginning of Write.
 2. A Write occurs during the overlap (t_{WP}) of a low $\overline{CE1}$, a high CE2 and a low \overline{WE} .
 3. t_{WR} is measured from the earliest of $\overline{CE1}$ or \overline{WE} going high or CE2 going low to the end of the Write cycle.
 4. If the $\overline{CE1}$ low transition or the CE2 high transition occurs simultaneously with the \overline{WE} low transition or after the \overline{WE} transition, outputs remain in a high impedance state.
 5. t_{CW} is measured from the later of \overline{CE} going low or CE2 going high to the end of Write.
 6. \overline{OE} is continuously low. ($\overline{OE} = V_{IL}$)
 7. Transition is measured $\pm 500\text{mV}$ from steady state. This parameter is sampled and not 100% tested.

AC Test Conditions

Input Pulse Levels	0V to 3.0V
Input Rise and Fall Time	5 ns
Input and Output Timing Reference Levels	1.5V
Output Load	See Figures 1 and 2


Figure 1. Output Load

Figure 2. Output Load for t_{LZ1} , t_{CLZ2} , t_{OLZ} , t_{CHZ1} , t_{CHZ2} , t_{OHZ} , t_{WHZ} , and t_{OW}
Data Retention Characteristics ($T_A = 0^\circ\text{C}$ to 70°C)

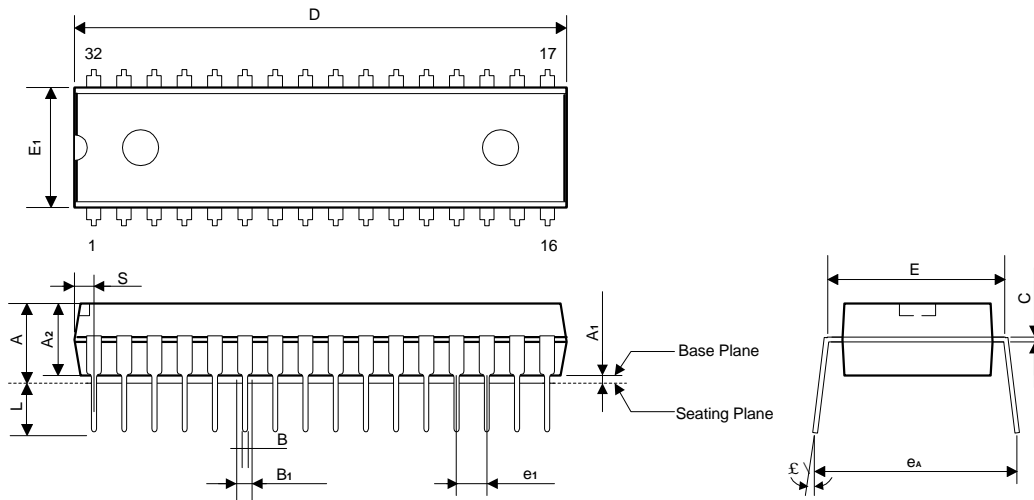
Symbol	Parameter	Min.	Max.	Unit	Conditions
V_{DR1}	VCC for Data Retention	3	5.25	V	$\overline{CE1} \geq VCC - 0.2V$ $CE2 \geq VCC - 0.2V$ or $CE2 \leq 0.2V$
V_{DR2}		3	5.25	V	$CE2 \leq 0.2V$ $\overline{CE1} \geq VCC - 0.2V$ or $\overline{CE1} \leq 0.2V$
I_{CCDR1}	Data Retention Current	-	5	mA	$VCC = 3.0V$ $\overline{CE1} \geq VCC - 0.2V$ $CE2 \geq VCC - 0.2V$ $V_{IN} \geq VCC - 0.2V$ or $V_{IN} \leq 0.2V$
I_{CCDR2}		-	5	mA	$VCC = 3.0V$ $CE2 \leq 0.2V$ $\overline{CE1} \leq 0.2V$ $V_{IN} \geq VCC - 0.2V$ or $V_{IN} \leq 0.2V$
t_{CDR}	Chip Disable to Data Retention Time	0	-	ns	See Retention Waveform
t_R	Operation Recovery Time	5	-	ms	

Low VCC Data Retention Waveform (1) $\overline{CE1}$ Controlled

Low VCC Data Retention Waveform (2) (CE2 Controlled)

Ordering Information

Part No.	Access Time (ns)	Operating Current Max. (mA)	Standby Current Max. (mA)	Package
UM61512AK-15	15	160	10	32L SKINNY
UM61512AK-20	20	160	10	32L SKINNY
UM61512AS-15	15	160	10	32L SOJ (300 mil)
UM61512AS-20	20	160	10	32L SOJ (300 mil)
UM61512ASW-15	15	160	10	32L SOJ (400 mil)
UM61512ASW-20	20	160	10	32L SOJ (400 mil)
UM61512AM-25	25	160	10	32L SOP
UM61512AV-15	15	160	10	32L TSOP

Package Information
SKINNY 32L Outline Dimensions

unit: inches/mm



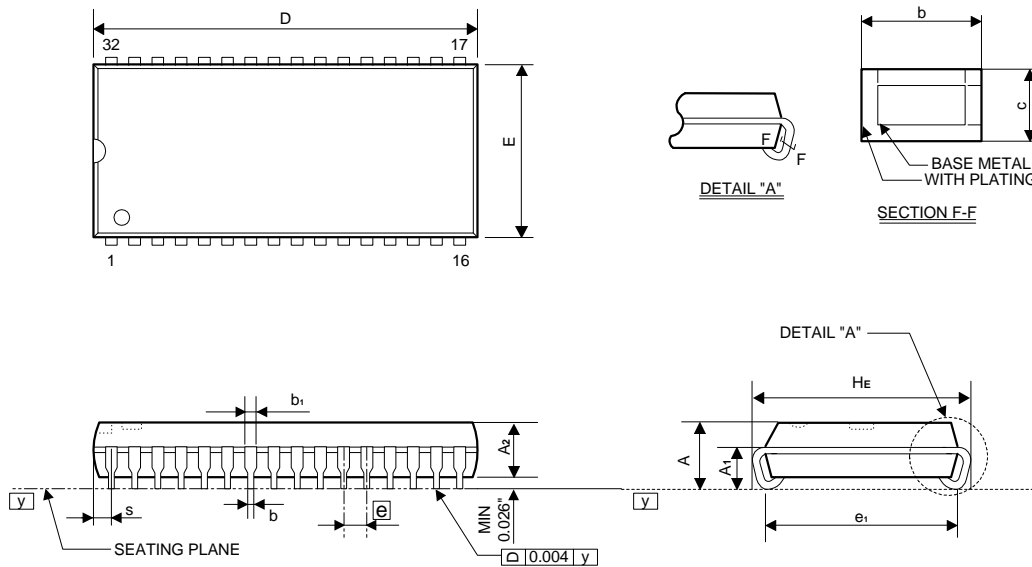
Symbol	Dimensions in inches	Dimensions in mm
A	0.200 Max.	5.08 Max.
A1	0.015 Min.	0.38 Min.
A2	0.130 _i \varnothing 010	3.30 _i \varnothing 25
B	0.018 +0.004 -0.002	0.46 +0.10 -0.05
B1	0.050 +0.004 -0.002	1.27 +0.10 -0.05
C	0.010 +0.004 -0.002	0.25 +0.10 -0.05
D	1.600 Typ. (1.620 Max.)	40.64 Typ. (41.15 Max.)
E	0.310 _i \varnothing 010	7.87 _i \varnothing 25
E1	0.288 Typ. (0.300 Max.)	7.32 Typ. (7.62 Max.)
e1	0.100 _i \varnothing 007	2.54 _i \varnothing 18
L	0.130 _i \varnothing 010	3.30 _i \varnothing 25
\angle	0° ~ 15°	0° ~ 15°
eA	0.355 _i \varnothing 035	9.02 _i \varnothing 89
S	0.059 Max.	1.50 Max.

Notes:

1. The maximum value of dimension D includes end flash.
2. Dimension E1 does not include resin fins.
3. Dimension S includes end flash.

Package Information
SOJ 32/32LD (300mil BODY) Outline Dimensions

unit: inches/mm



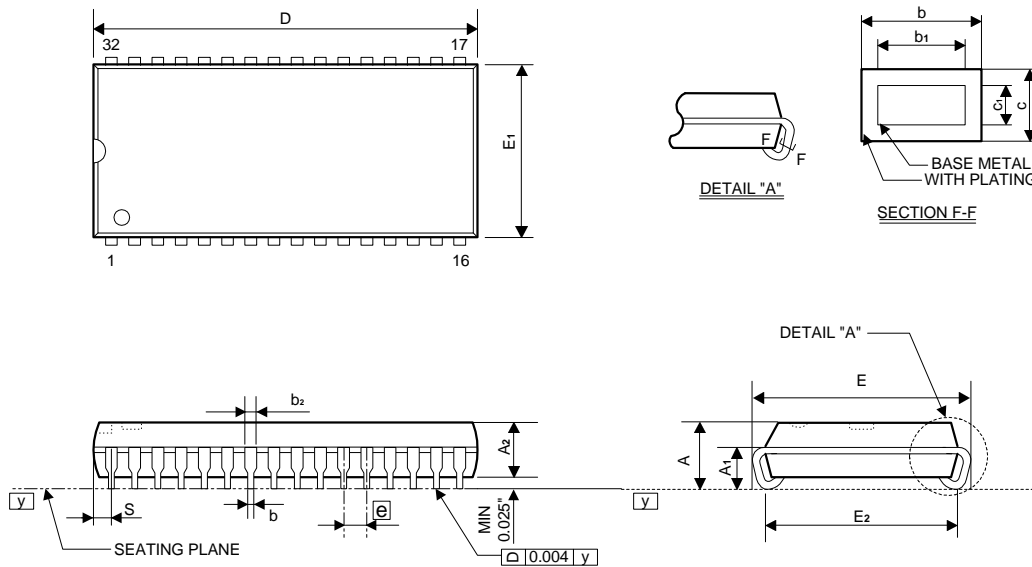
Symbol	Dimensions in inches			Dimensions in mm		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	0.128	0.132	0.140	3.25	3.35	3.56
A1	0.052	-	-	2.08	-	-
A2	0.095	0.100	0.105	2.41	2.54	2.67
b	0.016	0.018	0.020	0.41	0.46	0.51
b1	0.026	0.028	0.032	0.66	0.71	0.81
c	0.006	0.008	0.012	0.15	0.20	0.30
D	0.820	0.825	0.830	20.83	20.96	21.08
HE	0.330	0.335	0.340	8.39	8.51	8.63
E	0.295	0.300	0.305	7.49	7.62	7.75
e ₁	0.260	0.267	0.274	6.61	6.78	6.96
[e]	-	0.050	-	-	1.27	-
s	-	-	0.048	-	-	1.22
y	-	-	0.004	-	-	0.10

Notes:

1. The maximum value of dimension D includes end flash.
2. Dimension E doesn't include resin fins.
3. Dimension e₁ is for PC Board surface mount pad pitch design reference only.
4. Dimension S includes end flash.

Package Information
SOJ 32/32LD (400mil BODY) Outline Dimensions

unit: inches/mm



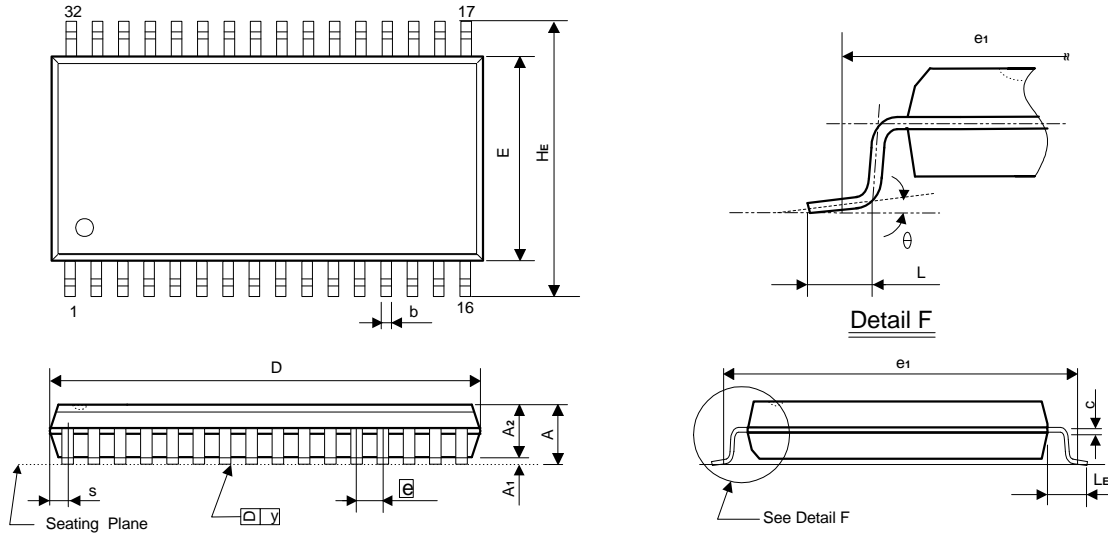
Symbol	Dimensions in inches			Dimensions in mm		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	0.131	0.138	0.145	3.35	3.51	3.68
A1	0.082	-	-	2.08	-	-
A2	0.105	0.110	0.115	2.67	2.79	2.91
b	0.016	0.018	0.020	0.41	0.46	0.51
b2	0.026	0.028	0.032	0.66	0.71	0.81
c	0.006	0.008	0.011	0.15	0.20	0.28
D	0.820	0.825	0.830	20.83	20.96	21.08
E	0.435	0.440	0.445	11.05	11.18	11.31
E1	0.395	0.400	0.405	10.03	10.16	10.29
E2	0.360	0.370	0.380	9.15	9.40	9.65
[e]	-	0.050	-	-	1.27	-
S	-	-	0.045	-	-	1.14
y	-	-	0.004	-	-	0.10

Notes:

1. Dimension D includes end flash.
2. Dimension E doesn't include resin fins.
3. Dimension E₁ is for PC Board surface mount pad pitch design reference only.
4. Dimension S includes end flash.

Package Information
SOP (W.B.) 32L Outline Dimensions

unit: inches/mm



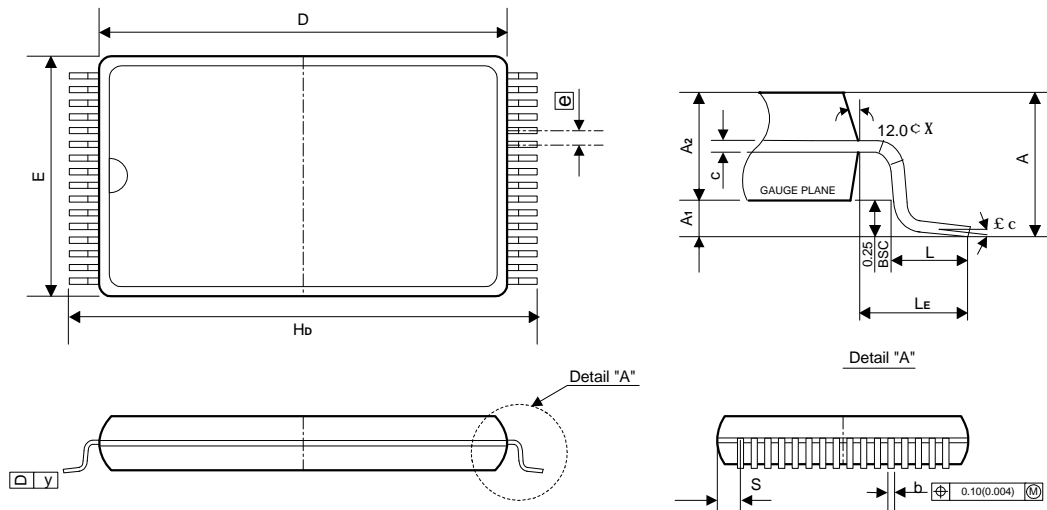
Symbol	Dimensions in inches	Dimensions in mm
A	0.118 Max.	3.00 Max.
A1	0.004 Min.	0.10 Min.
A2	0.106 _i \varnothing 005	2.69 _i \varnothing 13
b	0.016 +0.004 -0.002	0.41 +0.10 -0.05
c	0.008 +0.004 -0.002	0.20 +0.10 -0.05
D	0.805 Typ. (0.820 Max.)	20.45 Typ. (20.83 Max.)
E	0.445 _i \varnothing 10	11.30 _i \varnothing 25
\overline{e}	0.050 _i \varnothing 006	1.27 _i \varnothing 15
e ₁	0.525 NOM.	13.34 NOM.
HE	0.556 _i \varnothing 10	14.12 _i \varnothing 25
L	0.031 _i \varnothing 008	0.79 _i \varnothing 20
LE	0.055 _i \varnothing 008	1.40 _i \varnothing 20
S	0.044 Max.	1.12 Max.
y	0.004 Max.	0.10 Max.
θ	0° ~ 10°	0° ~ 10°

Notes:

1. The maximum value of dimension D includes end flash.
2. Dimension E does not include resin fins.
3. Dimension e₁ is for PC Board surface mount pad pitch design reference only.
4. Dimension S includes end flash.

Package Information
TSOP 32L TYPE I (8 X 20mm) Outline Dimensions

unit: inches/mm



Symbol	Dimensions in inches	Dimensions in mm
A	0.047 Max.	1.20 Max.
A ₁	0.004 _i Ø002	0.10 _i Ø05
A ₂	0.039 _i Ø002	1.00 _i Ø05
b	0.008 _i Ø001	0.20 _i Ø03
c	0.006 _i Ø001	0.15 _i Ø02
D	0.724 _i Ø004	18.40 _i Ø10
E	0.315 _i Ø004	8.00 _i Ø10
e	0.020 TYP.	0.50 TYP.
H _D	0.787 _i Ø007	20.00 _i Ø20
L	0.020 _i Ø004	0.50 _i Ø10
L _E	0.031 TYP.	0.80 TYP.
S	0.0167 TYP.	0.425 TYP.
Y	0.004 Max.	0.10 Max.
θ	0° ~ 6°	0° ~ 6°

Notes:

1. The maximum value of dimension D includes end flash.
2. Dimension E does not include resin fins.
3. Dimension e₁ is for PC Board surface mount pad pitch design reference only.
4. Dimension S includes end flash.